Product data sheet

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- · Low leakage current
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT
- High operating temperature capability (T_{j (max)} = 175°C)

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 129$ °C; Fig. 1; Fig. 2; Fig. 3	60		А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_{mb} ≤ 129 °C; square-wave pulse	120		А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600			А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	660			Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.6	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$		-	-	55	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A 001aaa020
2	Α	anode		001aaa020
mb	mb	mounting base; connected to cathode	1 2 TO-247 (SOD142)	

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV60W-600P	TO247	BYV60W-600PQ	Tube	30	SOD142	27-Nov-2012

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV60W-600P	BYV60W-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 129$ °C; Fig. 1; Fig. 2; Fig. 3	60	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse	120	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	660	А
l ² t	limiting Joule-integral	SIN; t _p = 10 ms	1800	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C

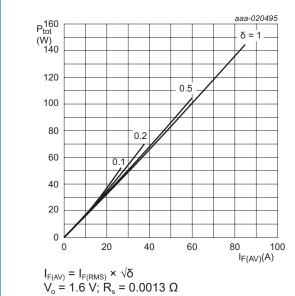
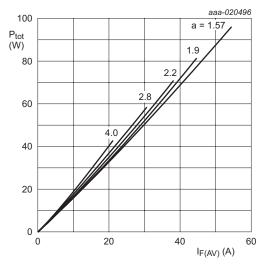


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.6 V; Rs = 0.0013 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

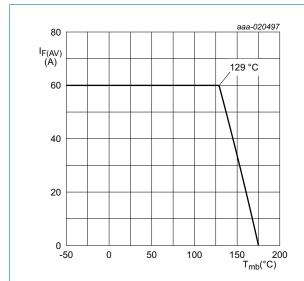


Fig. 3. Forward current as a function of mounting base temperature; maximum values

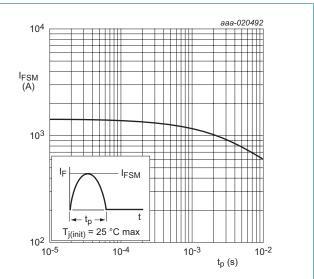
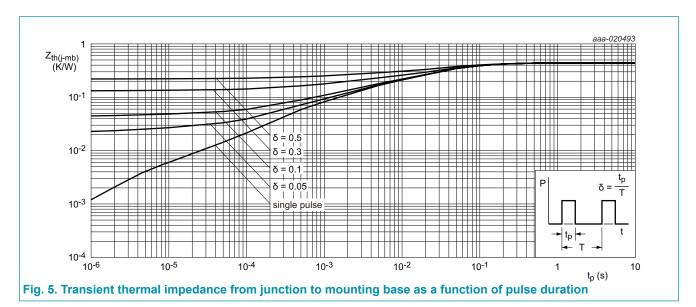


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

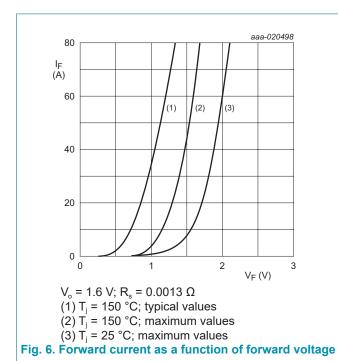
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.44	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics			'		
V_{F}	forward current	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μA
Dynamic	characteristics		,			
Q _r	reverse charge	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_J = 25 \text{ °C}; Fig. 7$	-	143	-	nC
		I _F = 60 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	876	-	nC
t _{rr} reverse re	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	55	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	53	-	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_J = 125 \text{ °C}; Fig. 7$	-	120	-	ns
I _{RM}	peak reverse recovery current	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_J = 25 \text{ °C}; Fig. 7$	-	5.4	-	А
		I _F = 60 A; V _R = 400 V; dI _F /dt = 200 A/µs; T _j = 125 °C; <u>Fig. 7</u>	-	14.5	-	А
E _{as}	non-repetitive avalanche energy	I _R = 2.2 A; T _{j(init)} = 25 °C; L = 40 mH	-	97	-	mJ



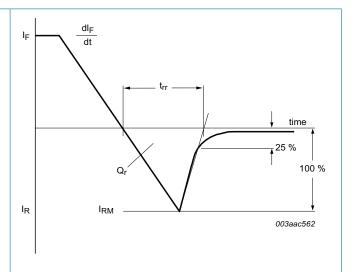
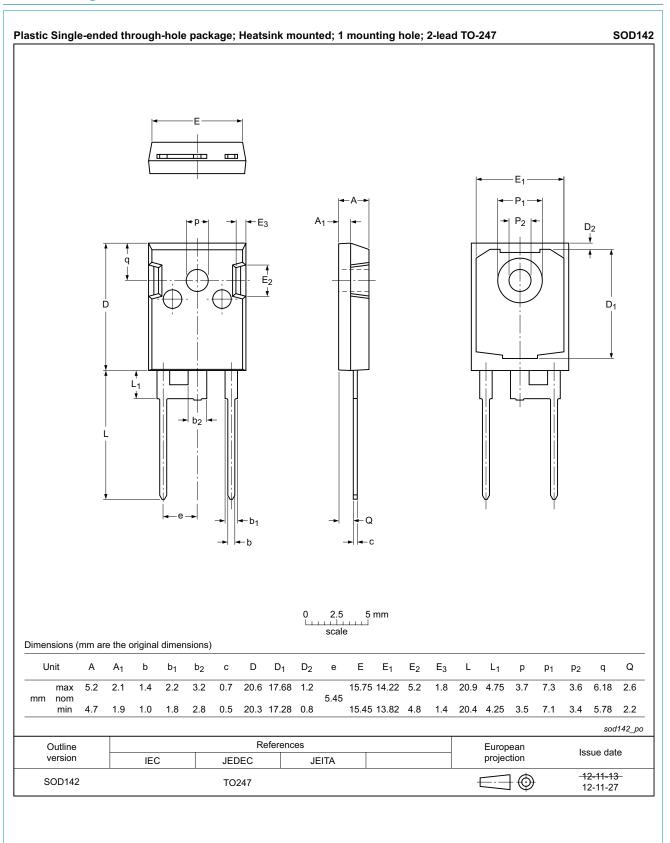


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BYV60W-600P

Ultrafast power diode

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	Features and benefits

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